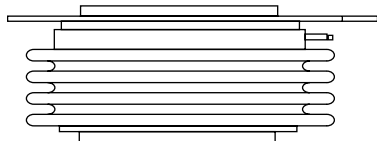


Phase Control Thyristors (Hockey PUK Version), 910 A



TO-200AC (B-PUK)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AC (B-PUK)
- Lead (Pb)-free
- Designed and qualified for industrial level



RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{T(AV)}$	910 A
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TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		910	A
	T_{hs}	55	°C
$I_{T(RMS)}$		1857	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	15 700	A
	60 Hz	16 400	
I^2t	50 Hz	1232	kA ² s
	60 Hz	1125	
V_{DRM}/V_{RRM}		1200 to 2000	V
t_q	Typical	150	μs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST700C..L	12	1200	1300	80
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	I _{T(AV)}	180° conduction, half sine wave double side (single side) cooled			910 (355)	A
					55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C heatsink temperature double side cooled			1857	A
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	15 700	
		t = 8.3 ms			16 400	
		t = 10 ms	100 % V _{RRM} reapplied		13 200	
		t = 8.3 ms			13 800	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		1232	kA ² s
		t = 8.3 ms			1125	
		t = 10 ms	100 % V _{RRM} reapplied		871	
		t = 8.3 ms			795	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			12 321	kA ² √s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			1.00	V
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			1.13	
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.40	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			0.35	
Maximum on-state voltage	V _{TM}	I _{pk} = 2000 A, T _J = T _J maximum, t _p = 10 ms sine pulse			1.80	V
Maximum holding current	I _H	T _J = 25 °C, anode supply 12 V resistive load			600	mA
Typical latching current	I _L				1000	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1 \text{ μs}$ $T_J = T_J \text{ maximum}$, anode voltage $\leq 80 \% V_{DRM}$	1000	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1 \text{ A/μs}$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 \text{ °C}$	1.0	μs
Typical turn-off time	t_q	$I_{TM} = 750 \text{ A}$, $T_J = T_J \text{ maximum}$, $di/dt = 60 \text{ A/μs}$, $V_R = 50 \text{ V}$, $dV/dt = 20 \text{ V/μs}$, gate 0 V 100 Ω, $t_p = 500 \text{ μs}$	150	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ maximum}$ linear to 80 % rated V_{DRM}	500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J \text{ maximum}$, rated V_{DRM}/V_{RRM} applied	80	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		10.0		W
Maximum average gate power	P _{G(AV)}	T _J = T _J maximum, f = 50 Hz, d% = 50		2.0		
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		3.0		A
Maximum peak positive gate voltage	+ V _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		20		V
Maximum peak negative gate voltage	- V _{GM}			5.0		
DC gate current required to trigger	I _{GT}	T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode-to-cathode applied	200	-	mA
		T _J = 25 °C		100	200	
		T _J = 125 °C		50	-	
DC gate voltage required to trigger	V _{GT}	T _J = - 40 °C		2.5	-	V
		T _J = 25 °C		1.8	3.0	
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V _{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum operating junction temperature range	T_J			- 40 to 125	°C
Maximum storage temperature range	T_{Stg}			- 40 to 150	
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled		0.073	K/W
		DC operation double side cooled		0.031	
Maximum thermal resistance, case to heatsink	R_{thC-hs}	DC operation single side cooled		0.011	
		DC operation double side cooled		0.006	
Mounting force, ± 10 %				14 700 (1500)	N (kg)
Approximate weight				255	g
Case style		See dimensions - link at the end of datasheet		TO-200AC (B-PUK)	

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.009	0.009	0.006	0.006	T _J = T _J maximum	K/W
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		
60°	0.020	0.020	0.021	0.021		
30°	0.036	0.036	0.036	0.036		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

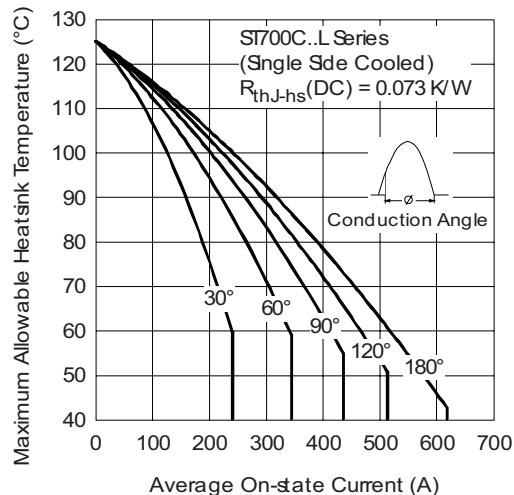


Fig. 1 - Current Ratings Characteristics

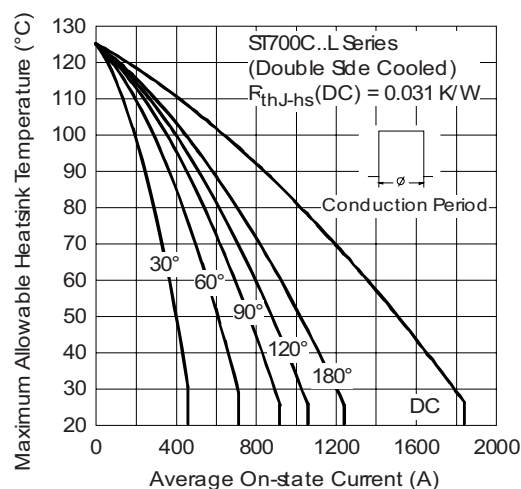


Fig. 4 - Current Ratings Characteristics

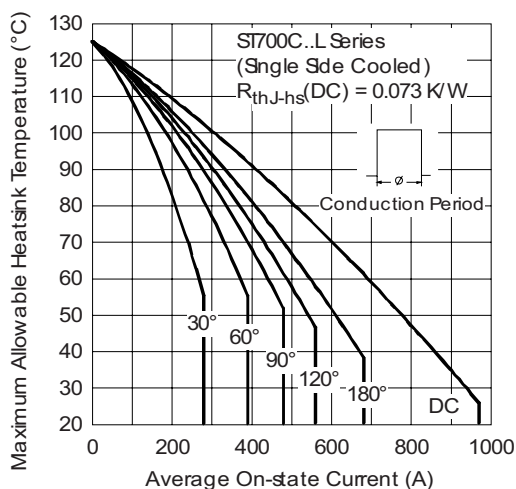


Fig. 2 - Current Ratings Characteristics

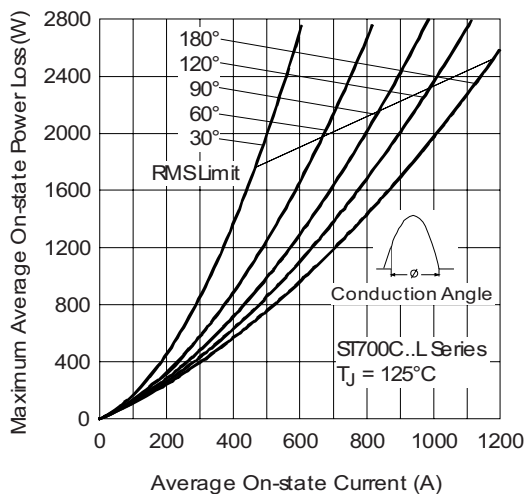


Fig. 5 - On-State Power Loss Characteristics

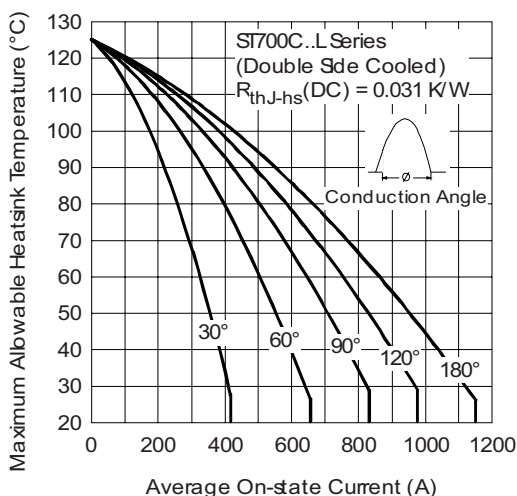


Fig. 3 - Current Ratings Characteristics

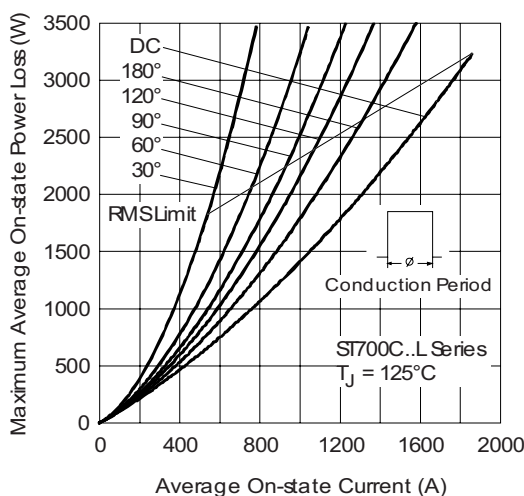


Fig. 6 - On-State Power Loss Characteristics

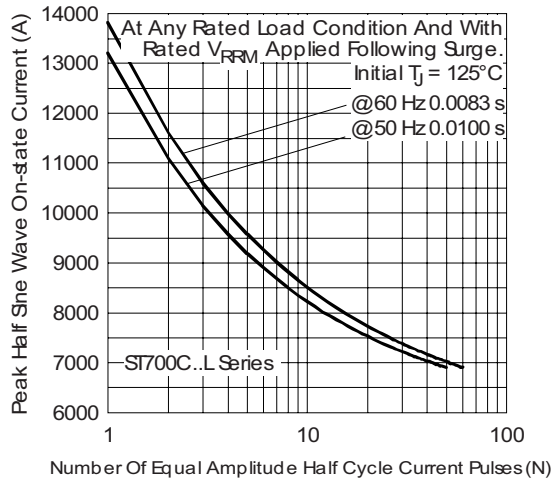


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

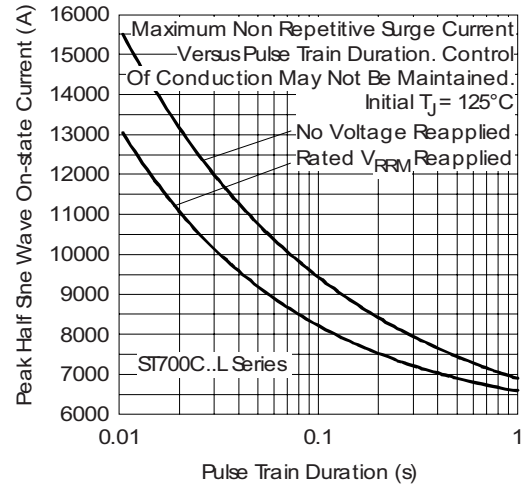


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

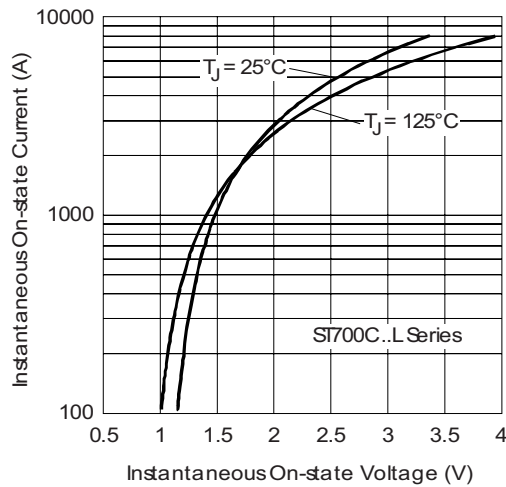


Fig. 9 - On-State Voltage Drop Characteristics

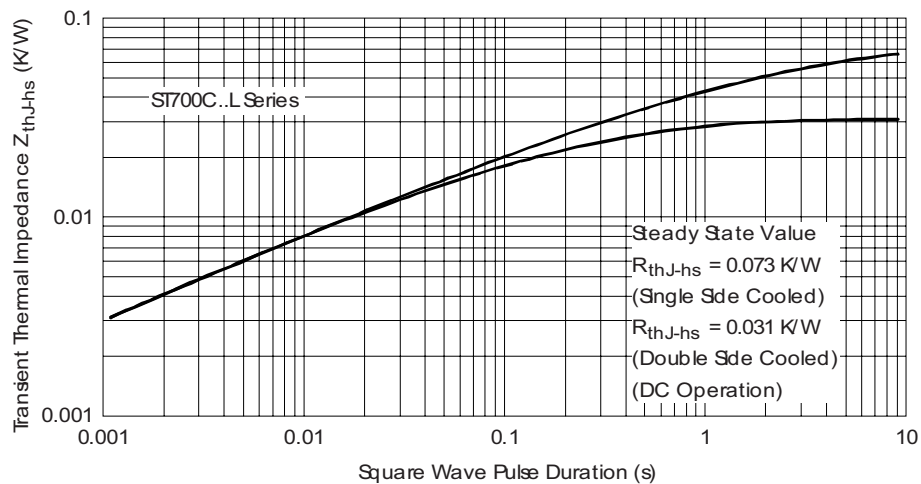


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

ST700CLPbF Series



Vishay High Power Products Phase Control Thyristors
(Hockey PUK Version), 910 A

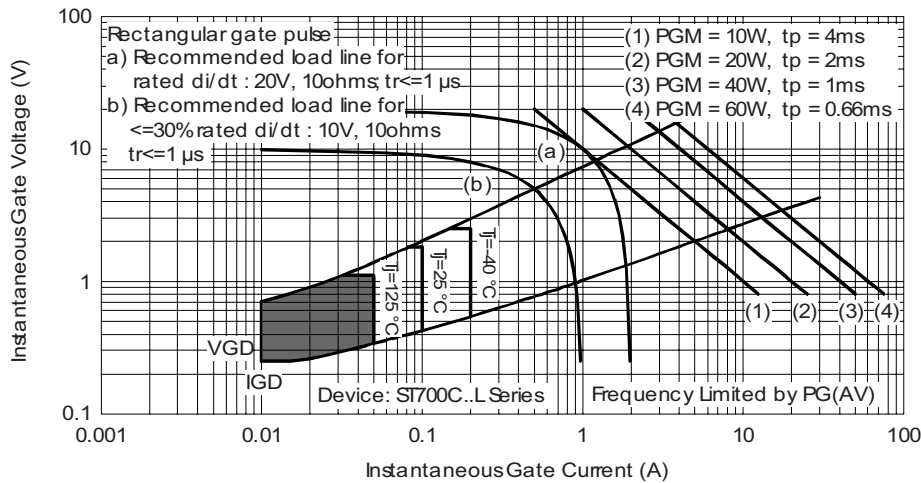


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	ST	70	0	C	20	L	1	-	PbF
	1	2	3	4	5	6	7	8	9
1	Thyristor								
2	Essential part number								
3	0 = Converter grade								
4	C = Ceramic PUK								
5	Voltage code x 100 = V_{RRM} (see Voltage Ratings table)								
6	L = PUK case TO-200AC (B-PUK)								
7	0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads) 1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads) 2 = Eyelet terminals (gate and auxiliary cathode soldered leads) 3 = Fast-on terminals (gate and auxiliary cathode soldered leads)								
8	Critical dV/dt : • None = 500 V/ μs (standard selection) • L = 1000 V/ μs (special selection)								
9	Lead (Pb)-free								

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95076



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